

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (currently amended): A transparent positive electrode for gallium nitride-based compound semiconductor light-emitting devices, comprising a contact metal layer in contact with a p-type semiconductor layer, a current diffusing layer on the contact metal layer, the current diffusing layer having an electrical conductivity larger than that of the contact metal layer, and a bonding pad layer on the current diffusing layer, wherein the thickness of the contact metal layer is from 0.1 to 7.5 nm.

2. (original): The transparent positive electrode according to claim 1, wherein the contact metal layer is a platinum group metal or an alloy containing a platinum group metal.

3. (original): The transparent positive electrode according to claim 2, wherein the contact metal layer is platinum.

4. *(canceled).*

5. (currently amended): The transparent positive electrode according to ~~claim 4~~ claim 1, wherein the thickness of the contact metal layer is from 0.1 to 5 nm.

6. (original): The transparent positive electrode according to claim 5, wherein the thickness of the contact metal layer is from 0.5 to 2.5 nm.

7. (previously presented): The transparent positive electrode according to claim 1, wherein the current diffusing layer is a metal selected from the group consisting of gold, silver and copper, or an alloy containing at least one member of gold, silver and copper.

8. (original): The transparent positive electrode according to claim 7, wherein the current diffusing layer is gold.

9. (previously presented): The transparent positive electrode according to claim 1, wherein the thickness of the current diffusing layer is from 1 to 20 nm.

10. (original): The transparent positive electrode according to claim 9, wherein the thickness of the current diffusing layer is from 1 to 10 nm.

11. (original): The transparent positive electrode according to claim 10, wherein the thickness of the current diffusing layer is from 3 to 6 nm.

12. (previously presented): A gallium nitride-based compound semiconductor light-emitting device comprising the transparent positive electrode according to claim 1.